

Silicon planar epitaxial N-channel high voltage switching field effect transistors
2П926А,Б with static induction and modulated channel conductivity.

1-source

2-drain

3-gate

Applicability, weight and type of package skipped
technical specs @ T=25C

1. $U_{сиmax}=U_{dsmax}, V$	450	400	
2. $U_{зсmax}=U_{gdmax}, V$	475	420	
3 $U_{зиmax}=U_{gsmax}, V$	-25	-30	(should be min)
4 $I_c=I_d \text{ max Continuous}, A$	16.5		
5 $I_c=I_d \text{ max Peak}, A$	30		
6 $I_z \text{ пр. max}=I_{gmax}, \text{ Continuous}, A$	2		
7 $I_z \text{ пр. max}=I_{gmax}, \text{ Peak}, A \text{ } t \leq 10\mu s$	4		
8 Total Device Dissipation, W	50		
9 Junction Temperature, $T_{пер}, \text{ max}, ^\circ C$	150		
10 $U_{зи} \text{ отс. } V, \text{ no less than}$	-15		

Gate-Source Cut-Off Voltage @ $I_d=3mA$

U_{ds} 2П926А=450V

U_{ds} 2П926Б=400V

11 Gate Reverse Current

@ $U_{зи}=U_{gs}=-15V \& U_{зс}=U_{gd}=-15V < 1mA$

12 Transconductance, S, mA/V 2000

13 Gate Reverse Current

@ $U_{зс}=U_{gd}=-475/420V < 1mA$

14 $R_{си. \text{ отк. }}=R_{dson}, \text{ Ohm}$ 0.1

@ $I_d=10A \& I_g=1A$

15 On/Off time, ns <100

@ $U_{ds}=300v @ I_d=2A$

16 Operating Temperature Range, $^\circ C$ -60+125

Business addresses and contacts skipped